

	Typ e	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
1	IS& R	2	("6184097").PN.	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 16 08:36		
2	BRS	0	advanced adj micro.as. and paton.in. and disposable.ti.	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 12 13:03		
3	BRS	0	(advanced adj micro.as. and paton.in. ) AND SMOS	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 12 13:04		
4	BRS	153	SMOS	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 12 13:04		
5	BRS	72	advanced adj micro.as. and paton.in.	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 12 13:12		
6	IS& R	4	(( "20030153161" ) or ("6365476")).PN.	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 13 11:20		
7	BRS	9	buried adj (si-ge or silicon adj germanium)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 13 11:30		

	Typ e	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
8	BRS	51	buried near5 (si-ge or silicon adj germanium)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 13 11:27		
9	BRS	35	enhanced near4 lateral adj diffusion	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 13 11:30		
10	BRS	3	(si-ge or silicon adj germanium) and (enhanced near4 lateral adj diffusion)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 13 11:28		
11	BRS	0	enhanced near4 lateral adj diffusion with compens\$5	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 13 11:30		
12	BRS	69	lateral adj diffusion with compens\$5	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 13 11:30		
13	BRS	35567	strained or si-ge or silicon adj germanium	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 13 11:30		
14	BRS	5	(lateral adj diffusion with compens\$5) and (strained or si-ge or silicon adj germanium)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 13 11:30		

	Typ e	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
15	BRS	263	strained adj silicon	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 15 14:47		
16	BRS	363	strained adj (silicon semiconductor)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 15 15:20		
17	BRS	1	strained adj (silicon semiconductor) and lateral adj diffusion	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 15 14:49		
18	BRS	8	strained adj (silicon semiconductor) and enhanc\$4 near5 diffusion	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 15 14:52		
19	BRS	6	second adj spacer with nmos	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 15 15:08		
20	BRS	28	5278441.URPN.	USPAT	2004/03/ 15 15:01		
21	BRS	18	enhanced adj lateral adj diffusion	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 15 15:11		
22	BRS	2	lateral adj diffusion with strain\$2	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 15 15:12		

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
23	BRS	1339	diffusion with strain\$2	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 15 15:12		
24	BRS	76	diffusion with strain\$2 same dopant\$1	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 15 15:12		
25	BRS	15	diffusion with strain\$2 same dopant\$1 and spacer	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 15 15:12		
26	BRS	19	diffusion with strain\$2 same dopant\$1 and spacer\$1	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 15 15:12		
27	BRS	120	(strained adj (silicon semiconductor)) and spacer\$1	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 16 09:44		
28	BRS	193	disposable adj spacer	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 16 08:37		
29	BRS	64175	(disposable adj spacer) and sige or si nearl ge or germanium	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 16 08:37		

	Typ e	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
30	BRS	62	(disposable adj spacer) and (sige or si nearl ge or germanium)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 16 08:37		
31	BRS	28	5278441.URPN.	USPAT	2004/03/ 16 09:13		
32	BRS	16	5654212.URPN.	USPAT	2004/03/ 16 09:18		
33	IS& R	476	(438/231).CCLS.	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 16 09:28		
34	BRS	27	((438/231).CCLS.) and (ge or si-ge or strained)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 16 09:28		
35	BRS	54	((438/231).CCLS.) and (ge or si-ge or strained or germanium)	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 16 09:28		
36	BRS	150	(strained adj (silicon semiconductor)) and CMOS	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 16 09:45		
37	BRS	29	5141890.URPN.	USPAT	2004/03/ 16 10:36		
38	IS& R	2	("6025266").PN.	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 18 10:48		

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
39	IS& R	2	("6025226").PN.	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 18 10:48		
40	IS& R	2	("6426250").PN.	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 18 15:54		
41	IS& R	2	("6307751").PN.	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM_TDB	2004/03/ 22 08:19		